The time has come to recognize the truth about this productive collaboration among scientists from France and the United States.

Dominique Stéhelin
Director,
Unite d'Oncologie Moleculaire, URA 1160,
Centre National de la Recherche Scientifique,
Institut Pasteur de Lille,
59019 Lille Cédex, France

References

1. D. Stéhelin, H. Varmus, M. Bishop, P. Vogt, *Nature* **260**, 170 (1976).

■

China's Internet Links

As someone who has worked at both the Chinese Academy of Sciences' (CAS's) Computer Network Center and at the Institute of High Energy Physics (IHEP) in Beijing, I would like to correct an error in Ted Plafker's article "China to triple Internet links with commercial hookups" (News & Comment, 13 Jan., p. 168). The link between the CAS's Computer Network Center and Stockton, California, provided by Sprint is not "the single connection available since last spring," as the article states; nor is it "China's first direct link to a U.S. Internet gateway."

The first direct academic link from China to the United States was a link between IHEP to the Stanford Linear Accelerator Center. It was provided jointly by the Chinese Ministry of Post and Telecommunication and AT&T. It became operational in March 1993 and was used to connect IHEP with the DECnet portion of the U.S. Department of Energy's Energy Sciences network (ESnet). In March 1994, this link also became an Internet link through a gateway at ESnet. In August 1994, the far end of the link was moved from the Stanford Linear Accelerator Center to KEK, the high energy physics center of Japan, making way for a future transition from satellite to terrestrial communication using underwater fiber optic cables. Since 1993, IHEP has provided many Chinese scientists with access—first electronic mail only and, later, full access—to the Internet. Both Hu Daoyuan and Qian Hualin used IHEP's service before CAS's link to the United States was established.

Xin Hao
IHEP Computing Center,
Post Office Box 918-7,
Beijing 100039,
People's Republic of China
E-mail: haoxin@bepc2.ihep.ac.cn

Zinc Selenide Lasers

In the Meeting Briefs of 22 April 1994, in a section entitled "Happy to see the blues" (Research News, p. 510), the work of Shuji Nakamura on gallium nitride blue light–emitting diodes (LEDs) was described, and comments were made about the rapid breakdown of zinc selenide lasers, "obviously rendering them useless for commercial applications." Gallium nitride blue light–emitting diodes should not be compared with lasers, because the conditions under which lasing occurs are vastly more demanding. The applied power density is much higher. Zinc selenide devices, when operated in the LED mode, show comparable lifetimes; these are steadily improving, as is common in the early stages of electronic devices.

Zinc selenide, as a laser, does indeed have serious problems; however, it is fundamentally a very rugged material (melting point, 1520°C). Laser action in the usable diode form has been positively established, and research solving the lifetime problems of these lasers is making rapid progress.

Brian J. Fitzpatrick
Optical Semiconductors, Inc.,
8 John Walsh Boulevard, Suite 421,
Peekskill, NY 10566, USA